

Shinji Migita

List of Publications by Year in descending order

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164
papers

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all docs

164
docs citations

164
times ranked

2438
citing authors

#	ARTICLE	IF	CITATIONS
1	Evolution of ferroelectric HfO ₂ in ultrathin region down to 3â€%nm. Applied Physics Letters, 2018, 112, .	1.5	188
2	Kinetic pathway of the ferroelectric phase formation in doped HfO ₂ films. Journal of Applied Physics, 2017, 122, .	1.1	150
3	Experimental evidence for the flatband voltage shift of high-k metal-oxide-semiconductor devices due to the dipole formation at the high-kâ•SiO ₂ interface. Applied Physics Letters, 2008, 92, .	1.5	140
4	Ferroelectric phase stabilization of HfO ₂ by nitrogen doping. Applied Physics Express, 2016, 9, 091501.	1.1	84
5	Polarization switching behavior of Hfâ€Zrâ€O ferroelectric ultrathin films studied through coercive field characteristics. Japanese Journal of Applied Physics, 2018, 57, 04FB01.	0.8	79
6	Fully coupled 3-D device simulation of negative capacitance FinFETs for sub 10 nm integration. , 2016, , .		77
7	Ferroelectricity of nondoped thin HfO ₂ films in TiN/HfO ₂ /TiN stacks. Japanese Journal of Applied Physics, 2016, 55, 08PB01.	0.8	68
8	Experimental Demonstration of Ultrashort-Channel (3 nm) Junctionless FETs Utilizing Atomically Sharp V-Grooves on SOI. IEEE Nanotechnology Magazine, 2014, 13, 208-215.	1.1	59
9	Study of tunneling transport in Si-based tunnel field-effect transistors with ON current enhancement utilizing isoelectronic trap. Applied Physics Letters, 2015, 106, .	1.5	54
10	Performance Enhancement of Tunnel Field-Effect Transistors by Synthetic Electric Field Effect. IEEE Electron Device Letters, 2014, 35, 792-794.	2.2	53
11	Thermodynamic control of ferroelectric-phase formation in Hf<i>x</i>Zr<i>1â•</i>O ₂ and ZrO ₂ . Journal of Applied Physics, 2018, 124, .	1.1	48
12	Comprehensive Study of V<inf>>FB<inf>> Shift in High-k CMOS - Dipole Formation, Fermi-level Pinning and Oxygen Vacancy Effect. , 2007, , .		39
13	Phase transformation behavior of ultrathin Hf_{0.5}Zr_{0.5}O₂ films investigated through wide range annealing experiments. Japanese Journal of Applied Physics, 2019, 58, SBBA07.	0.8	38
14	Self-limiting process for the bismuth content in molecular beam epitaxial growth of Bi ₂ Sr ₂ CuO _y thin films. Applied Physics Letters, 1997, 71, 3712-3714.	1.5	36
15	Unexpected equivalent-oxide-thickness dependence of the subthreshold swing in tunnel field-effect transistors. Applied Physics Express, 2014, 7, 024201.	1.1	35
16	Decomposition of On-Current Variability of nMOS FinFETs for Prediction Beyond 20 nm. IEEE Transactions on Electron Devices, 2012, 59, 2003-2010.	1.6	27
17	Electrical performances of junctionless-FETs at the scaling limit (L<inf>>CH<inf>>) T _j ETQq ₁ 1 0.784314 rgBT /Overlock 10 T ₅		25
18	A compact model for tunnel field-effect transistors incorporating nonlocal band-to-band tunneling. Journal of Applied Physics, 2013, 114, 144512.	1.1	25

#	ARTICLE	IF	CITATIONS
19	Epitaxial Bi ₄ Ti ₃ O ₁₂ thin film growth using Bi self-limiting function. Journal of Crystal Growth, 1999, 200, 161-168.	0.7	24
20	Re-examination of Flat-Band Voltage Shift for High-k MOS Devices. , 2007, , .		22
21	Intrinsic Origin of Electron Mobility Reduction in High-k MOSFETs - From Remote Phonon to Bottom Interface Dipole Scattering. , 2007, , .		22
22	Suppressing V_{th} and G_m variability of FinFETs using amorphous metal gates for 14 nm and beyond. , 2012, , .		22
23	Band-to-band tunneling current enhancement utilizing isoelectronic trap and its application to TFETs. , 2014, , .		22
24	Epitaxial structure SrTiO ₃ on Si. Journal of Applied Physics, 2001, 89, 5421-5424.	1.1	21
25	Symmetrical threshold voltage in complementary metal-oxide-semiconductor field-effect transistors with HfAlO _x (N) achieved by adjusting Hf/Al compositional ratio. Journal of Applied Physics, 2006, 99, 054506.	1.1	21
26	Fabrication and Demonstration of 3-nm-Channel-Length Junctionless Field-Effect Transistors on Silicon-on-Insulator Substrates Using Anisotropic Wet Etching and Lateral Diffusion of Dopants. Japanese Journal of Applied Physics, 2013, 52, 04CA01.	0.8	21
27	Design and demonstration of very high-k ($k_{eff} \approx 50$) HfO ₂ for ultra-scaled Si CMOS. , 2008, , .		20
28	Physical origins of mobility enhancement of Ge p-channel metal-insulator-semiconductor field effect transistors with Si passivation layers. Journal of Applied Physics, 2010, 108, 104511.	1.1	20
29	Material and device engineering in fully depleted silicon-on-insulator transistors to realize a steep subthreshold swing using negative capacitance. Japanese Journal of Applied Physics, 2016, 55, 08PD01.	0.8	20
30	Nanometer-scale crystallization of thin HfO ₂ films studied by HF-chemical etching. Applied Physics Letters, 2005, 86, 212907.	1.5	18
31	Achievement of Higher-k and High- ϵ_{eff} in Phase Controlled HfO ₂ Film Using Post Gate Electrode Deposition Annealing. ECS Transactions, 2007, 11, 35-45.	0.3	18
32	(111)-Faceted Metal Source and Drain for Aggressively Scaled Metal/High-k MISFETs. IEEE Transactions on Electron Devices, 2008, 55, 1244-1249.	1.6	18
33	Nature of interface traps in Ge metal-insulator-semiconductor structures with GeO ₂ interfacial layers. Journal of Applied Physics, 2011, 109, .	1.1	18
34	Experimental realization of complementary p- and n- tunnel FinFETs with subthreshold slopes of less than 60 mV/decade and very low ($\sim 10^{-3}$ A/m) off-current on a Si CMOS platform. , 2014, , .		18
35	Perspective of negative capacitance FinFETs investigated by transient TCAD simulation. , 2017, , .		17
36	Impact of Surface Hydrophilicization prior to Atomic Layer Deposition for HfO ₂ /Si Direct-Contact Gate Stacks. Applied Physics Express, 2009, 2, 011201.	1.1	16

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37	Tunnel Field-Effect Transistor with Epitaxially Grown Tunnel Junction Fabricated by Source/Drain-First and Tunnel-Junction-Last Processes. Japanese Journal of Applied Physics, 2013, 52, 04CC25.	0.8	16
38	Fringing field effects in negative capacitance field-effect transistors with a ferroelectric gate insulator. Japanese Journal of Applied Physics, 2018, 57, 04FD07.	0.8	16
39	Partial silicides technology for tunable work function electrodes on high-k gate dielectrics - fermi level pinning controlled PtS/sub X/, for HfO/sub X/(N) pMOSFET. , 0, , .		15
40	Suppression of threshold voltage variability of double-gate fin field-effect transistors using amorphous metal gate with uniform work function. Applied Physics Letters, 2013, 102, .	1.5	15
41	Introduction of SiGe/Si heterojunction into novel multilayer tunnel FinFET. Japanese Journal of Applied Physics, 2016, 55, 04EB06.	0.8	15
42	Tunnel FinFET CMOS inverter with very low short-circuit current for ultralow-power Internet of Things application. Japanese Journal of Applied Physics, 2017, 56, 04CD19.	0.8	15
43	Accelerated ferroelectric phase transformation in HfO ₂ /ZrO ₂ nanolaminates. Applied Physics Express, 2021, 14, 051006.	1.1	15
44	Particle-free superconducting Bi ₂ Sr ₂ CaCu ₂ O _x ultrathin films prepared by atomic-layer-controlled molecular beam epitaxy technique. Physica C: Superconductivity and Its Applications, 1999, 311, 42-48.	0.6	14
45	Memory properties of a ferroelectric gate field-effect transistor with an adjoining metal-ferroelectric-metal assistance cell. Journal of Applied Physics, 2003, 94, 2559-2562.	1.1	14
46	Accurate evaluation of Ge metal-insulator-semiconductor interface properties. Journal of Applied Physics, 2011, 110, .	1.1	14
47	Fabrication of Direct-Contact Higher-k HfO ₂ Gate Stacks by Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PG01.	0.8	14
48	Fin-Height Effect on Poly-Si/PVD-TiN Stacked-Gate FinFET Performance. IEEE Transactions on Electron Devices, 2012, 59, 647-653.	1.6	14
49	General relationship for cation and anion doping effects on ferroelectric HfO ₂ formation. , 2016, , .		14
50	Molecular beam epitaxial growth of SrO and CaO with RHEED intensity oscillation. Journal of Low Temperature Physics, 1996, 105, 1337-1342.	0.6	13
51	All-perovskite-oxide ferroelectric memory transistor composed of Bi ₂ Sr ₂ CuO _x and PbZr _{0.5} Ti _{0.5} O ₃ films. Journal of Applied Physics, 2001, 89, 8153-8158.	1.1	13
52	Pulsed laser deposition and ferroelectric properties of SrBi ₂ Ta ₂ O ₉ thin films. Materials Letters, 1999, 38, 406-412.	1.3	12
53	Influence of work function variation of metal gates on fluctuation of sub-threshold drain current for fin field-effect transistors with undoped channels. Japanese Journal of Applied Physics, 2014, 53, 04EC11.	0.8	12
54	Two-step annealing effects on ultrathin EOT higher-k (k=40) ALD-HfO ₂ gate stacks. Solid-State Electronics, 2013, 84, 58-64.	0.8	11

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55	The influence of Bi-sticking coefficient in the growth of Bi(2212) thin film by ion beam sputtering. Thin Solid Films, 1996, 281-282, 510-512.	0.8	10
56	Surface Morphology and Dielectric Properties of Stoichiometric and Off-Stoichiometric SrTiO ₃ Thin Films Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1999, 38, L1535-L1537.	0.8	10
57	Growth Style of Bi ₄ Ti ₃ O ₁₂ Thin Films on CeO ₂ /Ce _{0.12} Zr _{0.88} O ₂ Buffered Si Substrates. Japanese Journal of Applied Physics, 1999, 38, 5411-5416.	0.8	10
58	Fabrication and critical currents of thin-film-type Bi ₂ Sr ₂ CaCu ₂ O _x intrinsic Josephson junctions. Physica C: Superconductivity and Its Applications, 2001, 362, 256-260.	0.6	10
59	Enhancement of the ultraviolet absorption and Raman efficiencies of a few nanometer thick Si-on-insulator. Journal of Applied Physics, 2012, 112, 074317.	1.1	10
60	Accurate prediction of PBTI lifetime for N-type fin-channel tunnel FETs. , 2014, , .		10
61	Magnetic anomaly of Y _{1-x} Sr _x VO ₃ . Physica C: Superconductivity and Its Applications, 1999, 317-318, 464-470.	0.6	9
62	Predictivity of the non-local BTBT model for structure dependencies of tunnel FETs. , 2014, , .		9
63	Lowest variability SOI FinFETs having multiple V _t by back-biasing. , 2014, , .		9
64	Effect of hot implantation on ON-current enhancement utilizing isoelectronic trap in Si-based tunnel field-effect transistors. Applied Physics Express, 2015, 8, 036503.	1.1	9
65	Demonstrating performance improvement of complementary TFET circuits by I _{on} enhancement based on isoelectronic trap technology. , 2016, , .		9
66	Structural advantages of silicon-on-insulator FETs over FinFETs in steep subthreshold-swing operation in ferroelectric-gate FETs. Japanese Journal of Applied Physics, 2017, 56, 04CD10.	0.8	9
67	Multidomain Dynamics of Ferroelectric Polarization and its Coherency-Breaking in Negative Capacitance Field-Effect Transistors. , 2018, , .		9
68	Regulating phase transformation kinetics via redox reaction in ferroelectric Ge-doped HfO ₂ . Applied Physics Letters, 2020, 117, .	1.5	9
69	Gate-First Processed FUSI/HfO ₂ /HfSiO _x /Si MOSFETs with EOT=0.5 nm - Interfacial Layer Formation by Cycle-by-Cycle Deposition and Annealing. , 2007, , .		8
70	Impact of reduced pressure crystallization on ferroelectric properties in hafnium-zirconium dioxide films deposited by sputtering. Japanese Journal of Applied Physics, 2021, 60, SFFB05.	0.8	8
71	Structural Metastability and Size Scalability of Phase-Controlled HfO ₂ Formed through Cap-PDA. ECS Transactions, 2009, 19, 563-575.	0.3	7
72	Performance evaluation of parallel electric field tunnel field-effect transistor by a distributed-element circuit model. Solid-State Electronics, 2014, 102, 82-86.	0.8	7

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73	Impact of granular work function variation in a gate electrode on low-frequency noise for fin field-effect transistors. Applied Physics Express, 2015, 8, 044201.	1.1	7
74	Ultra-short channel junctionless transistor with a one-dimensional nanodot array floating gate. Applied Physics Letters, 2015, 106, .	1.5	7
75	Extremely Scaled ($\sim 1/40.2$ nm) Equivalent Oxide Thickness of Higher-k ($k=40$) HfO ₂ Gate Stacks Prepared by Atomic Layer Deposition and Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2012, 51, 02BA04.	0.8	7
76	Comparison between Bi-superconductor thin films fabricated via co-deposition and layer-by-layer deposition by ion beam sputtering method. Thin Solid Films, 1996, 281-282, 517-520.	0.8	6
77	Epitaxial Growth of Bi ₄ Ti ₃ O ₁₂ /CeO ₂ /Ce _{0.12} Zr _{0.88} O ₂ and Bi ₄ Ti ₃ O ₁₂ /SrTiO ₃ /Ce _{0.12} Zr _{0.88} O ₂ Thin Films on Si and Its Application to Metal-Ferroelectric-Insulator-Semiconductor Diodes. Japanese Journal of Applied Physics, 2000, 39, 5505-5511.	0.8	6
78	Silicon-Atom Induced Fermi-Level Pinning of Fully Silicided Platinum Gates on HfO ₂ Dielectrics. Japanese Journal of Applied Physics, 2005, 44, 2267-2272.	0.8	6
79	Study on Oxynitride Buffer Layers in HfO ₂ Metal-Insulator-Semiconductor Structures for Improving Metal-Insulator-Semiconductor Field-Effect Transistor Performance. Japanese Journal of Applied Physics, 2005, 44, 1698-1703.	0.8	6
80	AFM measurement of atomic-scale Si surface etching by active oxidation. Surface Science, 2010, 604, 1432-1437.	0.8	6
81	First demonstration of drain current enhancement in SOI tunnel FET with vertical-tunnel-multiplication. , 2012, , .		6
82	Improvement of epitaxial channel quality on heavily arsenic- and boron-doped Si surfaces and impact on performance of tunnel field-effect transistors. Solid-State Electronics, 2015, 113, 173-178.	0.8	6
83	Study of wake-up and fatigue properties in doped and undoped ferroelectric HfO ₂ in conjunction with piezo-response force microscopy analysis. , 2016, , .		6
84	Thickness-independent behavior of coercive field in HfO ₂ -based ferroelectrics. , 2017, , .		6
85	(Invited) Relationship between Ferroelectricity and Electrical Breakdown in Hf-Zr-O Thin Films. ECS Transactions, 2017, 80, 247-252.	0.3	6
86	Design points of ferroelectric field-effect transistors for memory and logic applications as investigated by metal-ferroelectric-metal-insulator-semiconductor gate stack structures using Hf _{0.5} Zr _{0.5} O ₂ films. Japanese Journal of Applied Physics, 2019, 58, SLLB06.	0.8	6
87	Thermal stability of ferroelectricity in hafnium-zirconium dioxide films deposited by sputtering and chemical solution deposition for oxide-channel ferroelectric-gate transistor applications. Applied Physics Express, 2021, 14, 041006.	1.1	6
88	Investigation of the wake-up process and time-dependent imprint of Hf _{0.5} Zr _{0.5} O ₂ film through the direct piezoelectric response. Applied Physics Letters, 2021, 119, .	1.5	6
89	Epitaxial structure SrBi ₂ Ta ₂ O ₉ / SrTiO ₃ / Ce _{0.12} Zr _{0.88} O ₂ / Si for ferroelectric-gate FET memory. Integrated Ferroelectrics, 2001, 40, 135-143.	0.3	5
90	Heated ion implantation technology for highly reliable metal-gate/high-k CMOS SOI FinFETs. , 2013, , .		5

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91	Comparative Study of Charge Trapping Type SOI-FinFET Flash Memories with Different Blocking Layer Materials. Journal of Low Power Electronics and Applications, 2014, 4, 153-167.	1.3	5
92	Robust and compact key generator using physically unclonable function based on logic-transistor-compatible poly-crystalline-Si channel FinFET technology. , 2015, , .		5
93	Suppression of tunneling rate fluctuations in tunnel field-effect transistors by enhancing tunneling probability. Japanese Journal of Applied Physics, 2017, 56, 04CD02.	0.8	5
94	Fabrication of Direct-Contact Higher- k HfO ₂ Gate Stacks by Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PG01.	0.8	5
95	Nanometer level etching and deposition of Bi-Sr-Ca-Cu-O superconducting thin films. , 1996, , .		4
96	Extremely Scaled (~ 0.2 nm) Equivalent Oxide Thickness of Higher- k ($k = 40$) HfO ₂ Gate Stacks Prepared by Atomic Layer Deposition and Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2012, 51, 02BA04.	0.8	4
97	Performance limit of parallel electric field tunnel FET and improvement by modified gate and channel configurations. , 2013, , .		4
98	Scaling breakthrough for analog/digital circuits by suppressing variability and low-frequency noise for FinFETs by amorphous metal gate technology. , 2014, , .		4
99	Variation behavior of tunnel-FETs originated from dopant concentration at source region and channel edge configuration. , 2014, , .		4
100	Importance of interface engineering for synthesis of SrHfO ₃ perovskite thin films on Si substrates through crystallization of amorphous films and control of flat-band voltages of metal-oxide-semiconductor capacitors. Japanese Journal of Applied Physics, 2014, 53, 04EA03.	0.8	4
101	(Invited) Charge Trapping Type SOI-FinFET Flash Memory. ECS Transactions, 2014, 61, 263-280.	0.3	4
102	Heated ion implantation for high-performance and highly reliable silicon-on-insulator complementary metal-oxide-silicon fin field-effect transistors. Japanese Journal of Applied Physics, 2015, 54, 04DA06.	0.8	4
103	Epitaxial growth of Ge thin film on Si (001) by DC magnetron sputtering. Materials Science in Semiconductor Processing, 2017, 70, 3-7.	1.9	4
104	Lateral variations of the surface electric potential and elastic stiffness of ultrathin Hf _{0.5} Zr _{0.5} O ₂ films on silicon. AIP Advances, 2021, 11, 015216.	0.6	4
105	Effect of Ge Metal-Insulator-Semiconductor Interfacial Layers on Interface Trap Density near the Conduction Band Edge. Japanese Journal of Applied Physics, 2010, 49, 04DA09.	0.8	3
106	(Invited) Epitaxial HfO ₂ Thin Films on Si Substrates: Strategy for Sub-1 nm EOT Technology. ECS Transactions, 2011, 41, 135-144.	0.3	3
107	Analysis of threshold voltage shifts in double gate tunnel FinFETs: Effects of improved electrostatics by gate dielectrics and back gate effects. , 2013, , .		3
108	Impact of fin length on threshold voltage modulation by back bias for Independent double-gate tunnel fin field-effect transistors. Solid-State Electronics, 2015, 111, 62-66.	0.8	3

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109	Impact of extension implantation conditions of fin field-effect transistors on gate-induced drain leakage. Japanese Journal of Applied Physics, 2016, 55, 04EB01.	0.8	3
110	Impact of residual defects caused by extension ion implantation in FinFETs on parasitic resistance and its fluctuation. Solid-State Electronics, 2017, 132, 103-108.	0.8	3
111	Simulation study of short-channel effects of tunnel field-effect transistors. Japanese Journal of Applied Physics, 2018, 57, 04FD04.	0.8	3
112	Device Simulation of Negative-Capacitance Field-Effect Transistors With a Ferroelectric Gate Insulator. , 2018, , .		3
113	Growth mechanism of epitaxial NiSi ₂ in atomic-scale for Schottky source/drain in Silicon Nanowire transistors. , 2009, , .		2
114	Cryogenic operation of double-gate FinFET and demonstration of analog circuit at 4.2K. , 2012, , .		2
115	TDDB characteristics of thin polycrystalline and amorphous HfO ₂ films. , 2014, , .		2
116	Experimental study of three-dimensional fin-channel charge trapping flash memories with titanium nitride and polycrystalline silicon gates. Japanese Journal of Applied Physics, 2014, 53, 04ED16.	0.8	2
117	Fluctuation in drain induced barrier lowering (DIBL) for FinFETs caused by granular work function variation of metal gates. , 2014, , .		2
118	Understanding of BTI for tunnel FETs. , 2015, , .		2
119	Steep subthreshold swing and energy efficiency in MOSFETs utilizing nonlinear gate dielectric insulators. Japanese Journal of Applied Physics, 2016, 55, 04ED02.	0.8	2
120	On the drain bias dependence of long-channel silicon-on-insulator-based tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CD04.	0.8	2
121	Bias temperature instability in tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CA04.	0.8	2
122	Design of steep-slope negative-capacitance FinFETs for dense integration: Importance of appropriate ferroelectric capacitance and short-channel effects. Japanese Journal of Applied Physics, 2018, 57, 04FD03.	0.8	2
123	Assessment of Steep-Subthreshold Swing Behaviors in Ferroelectric-Gate Field-Effect Transistors Caused by Positive Feedback of Polarization Reversal. , 2018, , .		2
124	One-dimensional array of gold nanoparticles fabricated using biotemplate and its application to fine FET. Japanese Journal of Applied Physics, 2018, 57, 06HC05.	0.8	2
125	Channel shape and interpoly dielectric material effects on electrical characteristics of floating-gate-type three-dimensional fin channel flash memories. Japanese Journal of Applied Physics, 2015, 54, 04DD04.	0.8	2
126	Enhancement of ferroelectricity in sputtered HZO thin films by catalytically generated atomic hydrogen treatment. Japanese Journal of Applied Physics, 2022, 61, SH1004.	0.8	2

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127	Evaluation of Ozone Condensation System by Thermal Decomposition Method. Japanese Journal of Applied Physics, 1997, 36, 94-97.	0.8	1
128	Fabrication and Electrical Characteristics of a Trench-Type Metal-Ferroelectric-Metal-Insulator-Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2001, 40, 5605-5609.	0.8	1
129	Exact control of junction position using epitaxial NiSi ₂ crystallization in ultrathin silicon-on-insulator metal-oxide-semiconductor field-effect transistors. AIP Advances, 2012, 2, .	0.6	1
130	Impact of atomic-scale structural design on ultra-short channel (3 nm) MOSFETs. , 2013, , .		1
131	Variability of short channel junctionless field-effect transistors caused by fluctuation of dopant concentration. , 2013, , .		1
132	Guidelines for symmetric threshold voltage in tunnel FinFETs with single and dual metal gate electrodes. , 2013, , .		1
133	Fabrication and characterization of 3D fin-channel MANOS type flash memory. , 2014, , .		1
134	Study of gate leakage current paths in p-channel tunnel field-effect transistor by current separation measurement and device simulation. Japanese Journal of Applied Physics, 2015, 54, 034202.	0.8	1
135	PBTI for N-type tunnel FinFETs. , 2015, , .		1
136	Design and simulation of steep-slope silicon-on-insulator FETs using negative capacitance: Impact of buried oxide thickness and remnant polarization. , 2016, , .		1
137	Charge effects of ultrafine FET with nanodot type floating gate. , 2016, , .		1
138	(Invited) Floating Gate Type SOI-FinFET Flash Memories with Different Channel Shapes and Interpoly Dielectric Materials. ECS Transactions, 2016, 72, 11-24.	0.3	1
139	Device simulation of negative-capacitance field-effect transistors with a uniaxial ferroelectric gate insulator. Nonlinear Theory and Its Applications IEICE, 2020, 11, 145-156.	0.4	1
140	Impact of annealing on electric and elastic properties of 10-nm Hf _{0.5} Zr _{0.5} O ₂ films prepared on Si by sputtering. Microelectronic Engineering, 2022, 258, 111770.	1.1	1
141	Superconductivity and magnetic transitions of La ₂ â ^x CuO _y system under 60kbar O ₂ -HIP treatment. Physica C: Superconductivity and Its Applications, 1991, 185-189, 775-776.	0.6	0
142	Molecular beam epitaxial growth of BSCCO and Bi-based oxides: self-limiting growth of the Bi element. , 1998, , .		0
143	Fabrication and electrical properties of ferroelectric-gate FETS with epitaxial gate structures. Electronics and Communications in Japan, 2004, 87, 24-33.	0.2	0
144	Impact of Minority Carrier Response on Characterization of Ge MIS Interface Traps. ECS Transactions, 2009, 19, 117-128.	0.3	0

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145	Inversion Layer Mobility in High-k Dielectric MOSFETs - Intrinsic Mobility Degradation by Electric Dipoles at High-k/SiO ₂ Interface. ECS Transactions, 2009, 16, 67-75.	0.3	0
146	Influence of fin height on poly-Si/PVD-TiN stacked gate FinFET performance. , 2011, , .		0
147	Two-step annealing effects on ultrathin EOT higher-k (k = 40) ALD-HfO ₂ gate stacks. , 2012, , .		0
148	Experimental Comparisons between Tetrakis(dimethylamino)titanium Precursor-Based Atomic-Layer-Deposited and Physical-Vapor-Deposited Titaniumâ€“Nitride Gate for High-Performance Fin-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DA05.	0.8	0
149	Extremely Scaled Equivalent Oxide Thickness of High-k (k=40) HfO ₂ Gate Stacks Prepared by Atomic Layer Deposition and Ti Cap Anneal. Hyomen Kagaku, 2012, 33, 610-615.	0.0	0
150	Analysis of V _{th} flexibility in ultrathin-BOX SOI FinFETs. , 2013, , .		0
151	(Invited) Extremely Short Channel Si-MOSFETs Prepared on SOI Substrates Using Anisotropic Wet Etching. ECS Transactions, 2013, 58, 273-280.	0.3	0
152	Suppressed variability of current-onset voltage of FinFETs by improvement of work function uniformity of metal gates. , 2013, , .		0
153	Experimental study of charge trapping type FinFET flash memory. , 2014, , .		0
154	Modeling of parallel electric field tunnel FETs. , 2015, , .		0
155	Highly V _t tunable and low variability triangular fin-channel MOSFETs on SOTB. Microelectronic Engineering, 2015, 147, 290-293.	1.1	0
156	Evolution of nanoscale silicon CMOS technology for ultra low power application. , 2015, , .		0
157	Structural and electrical characterization of epitaxial Ge thin films on Si(001) formed by sputtering. Japanese Journal of Applied Physics, 2017, 56, 04CB01.	0.8	0
158	Estimation of charge effects of ultrafine channel utilizing junctionless transistor with nanodot-type floating gate. Japanese Journal of Applied Physics, 2017, 56, 03BB05.	0.8	0
159	Ultrashort intrinsic-like channel FETs with nanodot-type floating gate utilizing biomaterial. Japanese Journal of Applied Physics, 2018, 57, 125003.	0.8	0
160	Ferroelectric Films by Physical Vapor Deposition and Ion Implantation. , 2019, , 103-125.		0
161	Fabrication of High-k Gate Insulator Films by Atomic Layer Deposition and Their Properties Influenced by Substrate Hydrophilicity. Journal of the Vacuum Society of Japan, 2011, 54, 105-109.	0.3	0
162	One-dimensional arrangement of nanoparticles utilizing the V-groove and cage shaped proteins. Japanese Journal of Applied Physics, 2017, 56, 06GG11.	0.8	0

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163	Robustness of Ferroelectricity in Hafnium-Zirconium Dioxide Films Deposited By Sputtering and Chemical Solution Deposition for Ferroelectric Transistor Applications. ECS Meeting Abstracts, 2020, MA2020-02, 1371-1371.	0.0	0
164	Anomalous change of carrier transport property of ferroelectric Hf _{0.5} Zr _{0.5} O ₂ thin films in the first poling treatment. Japanese Journal of Applied Physics, 0, , .	0.8	0